

**Features**

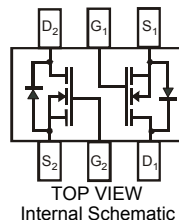
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **"Green" Device (Note 3 and 4)**

**Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



SOT-363


**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$	$V_{DGR}$	60	V
Gate-Source Voltage	$V_{GSS}$	Continuous	$\pm 20$
		Pulsed	$\pm 40$
Drain Current (Note 1)	$I_D$	Continuous	115
		Continuous @ $100^\circ\text{C}$	73
		Pulsed	800

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	$P_d$	200	mW
Derating above $T_A = 25^\circ\text{C}$ (Note 1)		1.60	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0 500	μA	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.2 4.4	7.5 13.5	Ω	@ T <sub>J</sub> = 25°C @ T <sub>J</sub> = 125°C V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.05A V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.0	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iSS</sub>	—	22	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oSS</sub>	—	11	25	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	2.0	5.0	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.0	20	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>L</sub> = 150Ω, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	11	20	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

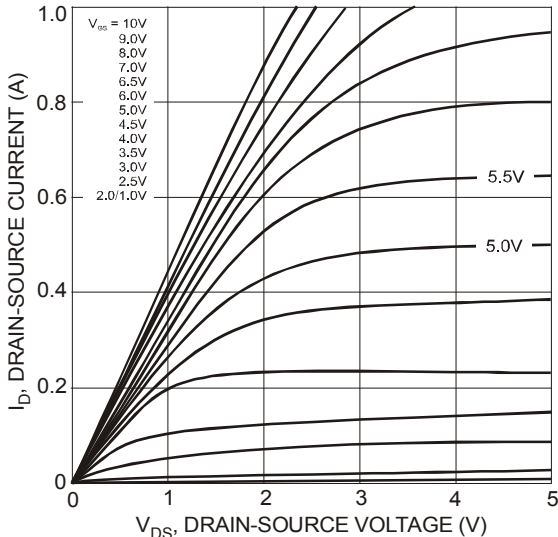


Fig. 1 On-Region Characteristics

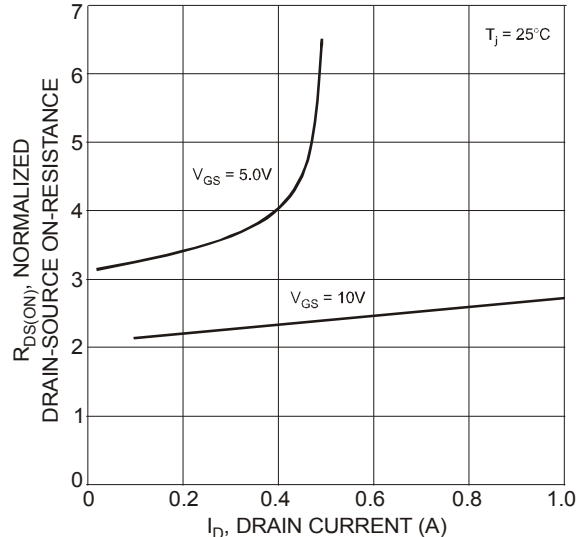


Fig. 2 On-Resistance vs. Drain Current

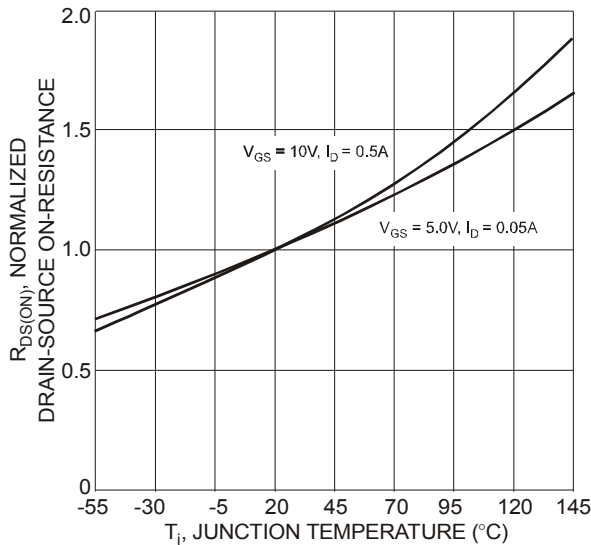


Fig. 3 On-Resistance vs. Junction Temperature

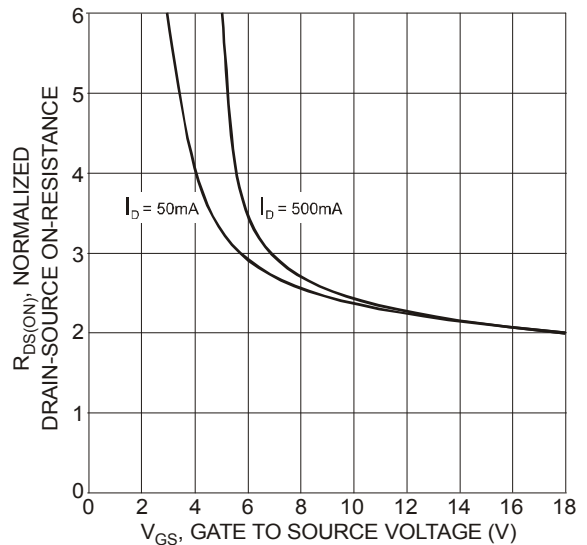


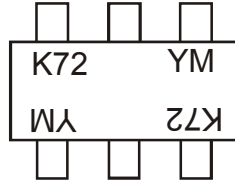
Fig. 4 On-Resistance vs. Gate-Source Voltage

**Ordering Information** (Note 6)

Part Number	Case	Packaging
2N7002DW-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



K72 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

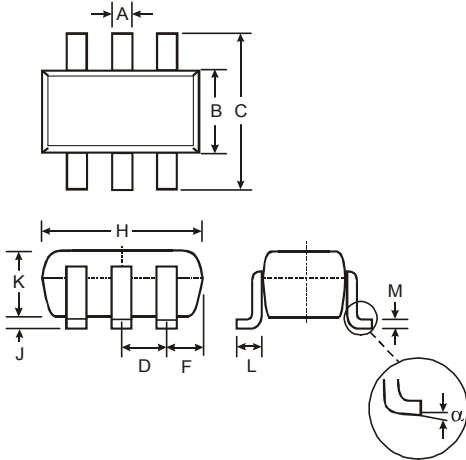
Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

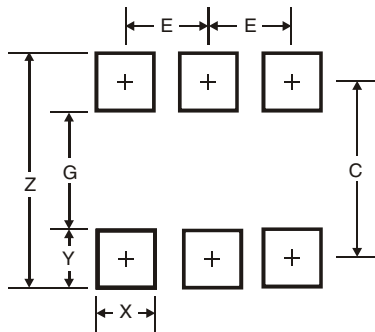
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
alpha	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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